Functional Safety Information

INA225-Q1 Functional Safety FIT Rate, Failure Mode Distribution and Pin FMA



1 Overview

This document contains information for the INA225-Q1 (VSSOP-8 package) to aid in a functional safety system design. Information provided are:

- Functional Safety Failure In Time (FIT) rates of the semiconductor component estimated by the application of industry reliability standards
- Component failure modes and their distribution (FMD) based on the primary function of the device

Figure 1-1 shows the device functional block diagram for reference.

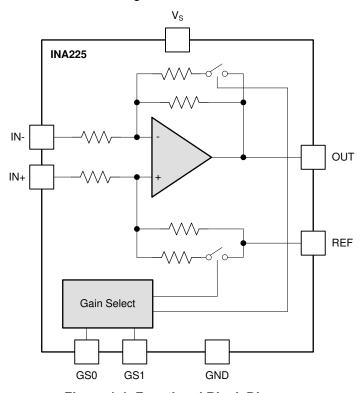


Figure 1-1. Functional Block Diagram

The INA225-Q1 was developed using a quality-managed development process, but was not developed in accordance with the IEC 61508 or ISO 26262 standards.



2 Functional Safety Failure In Time (FIT) Rates

This section provides Functional Safety Failure In Time (FIT) rates for the INA225-Q1 based on two different industry-wide used reliability standards:

- Table 2-1 provides FIT rates based on IEC TR 62380 / ISO 26262 part 11
- Table 2-2 provides FIT rates based on the Siemens Norm SN 29500-2

Table 2-1. Component Failure Rates per IEC TR 62380 / ISO 26262 Part 11

FIT IEC TR 62380 / ISO 26262	FIT (Failures Per 10 ⁹ Hours)
Total Component FIT Rate	7
Die FIT Rate	3
Package FIT Rate	4

The failure rate and mission profile information in Table 2-1 comes from the Reliability data handbook IEC TR 62380 / ISO 26262 part 11:

Mission Profile: Motor Control from Table 11

· Power dissipation: 15 mW

Climate type: World-wide Table 8Package factor (lambda 3): Table 17b

· Substrate Material: FR4

· EOS FIT rate assumed: 0 FIT

Table 2-2. Component Failure Rates per Siemens Norm SN 29500-2

Table	Category	Reference FIT Rate	Reference Virtual T _J
4	BICMOS Op Amp, Comparators, Voltage Monitors	8 FIT	45°C

The Reference FIT Rate and Reference Virtual T_J (junction temperature) in Table 2-2 come from the Siemens Norm SN 29500-2 tables 1 through 5. Failure rates under operating conditions are calculated from the reference failure rate and virtual junction temperature using conversion information in SN 29500-2 section 4.



3 Failure Mode Distribution (FMD)

The failure mode distribution estimation for INA225-Q1 in Table 3-1 comes from the combination of common failure modes listed in standards such as IEC 61508 and ISO 26262, the ratio of sub-circuit function size and complexity and from best engineering judgment.

The failure modes listed in this section reflect random failure events and do not include failures due to misuse or overstress.

Table 3-1. Die Failure Modes and Distribution

Die Failure Modes	Failure Mode Distribution (%)
OUT open (Hi-Z)	15%
OUT to GND	25%
OUT to VS	25%
OUT functional, not in specification	30%
Gain select fault	5%



4 Pin Failure Mode Analysis (Pin FMA)

This section provides a Failure Mode Analysis (FMA) for the pins of the INA225-Q1. The failure modes covered in this document include the typical pin-by-pin failure scenarios:

- Pin short-circuited to Ground (see Table 4-2)
- Pin open-circuited (see Table 4-3)
- Pin short-circuited to an adjacent pin (see Table 4-4)
- Pin short-circuited to supply (see Table 4-5)

through also indicate how these pin conditions can affect the device as per the failure effects classification in .

Table 4-1.	TI Class	sification	of Failure	Fffocts.
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Class Failure Effects	
A	Potential device damage that affects functionality
B No device damage, but loss of functionality	
С	No device damage, but performance degradation
D	No device damage, no impact to functionality or performance

shows the INA225-Q1 pin diagram. For a detailed description of the device pins please refer to the *Pin Configuration and Functions* section in the *Device Name* data sheet.

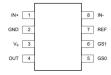


Figure 4-1. Pin Diagram

Following are the assumptions of use and the device configuration assumed for the pin FMA in this section:

- $T_A = -40^{\circ}C \text{ to } +125^{\circ}C$
- V_S = 5 V
- V_{IN+} = 12 V
- V_{REF} = V_S /2

Table 4-2. Pin FMA for Device Pins Short-Circuited to Ground

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
IN+	In high-side configuration, a short from the bus supply to GND will occur. High current will flow from bus supply to ground. In low side configuration, input pins are shorted.		В
GND	2	Normal Operation.	D
V _S	3	Power supply shorted to ground.	В
OUT	4	Output shorts to ground. When left in this configuration for a long time, under high supplies self heating could cause dice junction temperature to exceed 150 degrees Celsius.	В
GS0	5	If intended connection is anything other than GND, functionality will be affected.	D if GS0=GND by design; C otherwise
GS1	6	If intended connection is anything other than GND, functionality will be affected.	D if GS1=GND by design; C otherwise
REF	7	If intended connection is anything other than GND, functionality will be affected.	D if REF=GND by design; C otherwise
IN-	8	In high-side configuration, a short from the bus supply to GND will occur. High current will flow from bus supply to ground. In low side configuration, normal operation.	B for High side or D for low side



Table 4-3. Pin FMA for Device Pins Open-Circuited

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
IN+	1	Differential input voltage is not well defined.	В
GND	2	GND is floating. Output will be incorrect as it is no longer referenced to GND.	В
Vs	3	No power supply to device. Device may be biased through inputs. Output will be close to GND.	В
OUT	4	Output can be left open, there is no effect on the IC.	В
GS0	5	Device gain is not defined	С
GS1	6	Device gain is not defined	С
REF	7	Device loses reference voltage.	С
IN-	8	Differential input voltage is not well defined.	В

Table 4-4. Pin FMA for Device Pins Short-Circuited to Adjacent Pin

Pin Name	Pin No.	Shorted to	Description of Potential Failure Effect(s)	Failure Effect Class
IN+	1	GND	In high-side configuration, a short from the bus supply to GND will occur. High current will flow from bus supply to ground. In low side configuration, normal operation.	В
GND	2	V _S	Power supply shorted to ground	В
V _S	3	OUT	Output shorts to supply. When left in this configuration for a long time, under high supplies self heating could cause dice junction temperature to exceed 150 degrees Celsius.	В
OUT	4	GS0	Device gain is not defined.	С
GS0	5	GS1	Device gain maybe different than desired.	С
GS1	6	REF	Device gain maybe different than desired.	С
REF	7	IN-	If high voltage (>Vs+0.3V) is present, damage will occur.	А
IN-	8	IN+	Input differential voltage=0V.	С

Table 4-5. Pin FMA for Device Pins Short-Circuited to Supply

Pin Name	Pin No.	Description of Potential Failure Effect(s)	Failure Effect Class
IN+	In high-side configuration, a short from the bus supply to VS will occur. IN+ 1 High current will flow from bus supply to VDor vice versa. Device could be damaged.		A for High side or B for low side
GND	2	Power supply shorted to GND	В
V _S	3	Normal operation.	D
OUT	4	Output shorts to supply. When left in this configuration for a long time, under high supplies self heating could cause dice junction temperature to exceed 150 degrees Celsius.	В
GS0	5	If intended connection is anything other than VS, functionality will be affected.	D if GS0=VS by design; C otherwise
GS1	6	If intended connection is anything other than VS, functionality will be affected.	D if GS1=VS by design; C otherwise
REF	7	If intended connection is anything other than VS, functionality will be affected.	D if REF=VS by design; C otherwise
IN-	8	In high-side configuration, a short from the bus supply to VS will occur. High current will flow from bus supply to VS or vice versa. Device could be damaged.	A for High side or B for low side



Revision History www.ti.com

5	Rev	visio	n H	istory
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NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	Changes from Revision * (June 2020) to Revision A (September 2020)	Page
•	Added Pin Failure Mode Analysis (Pin FMA) section	4

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